(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
16 April 2026 (16.04.2026)

WIPO | PCT

(10) International Publication Number
WO 2026/076911 A1

(51) International Patent Classification:
G11C 7/10 (2006.01) *H01L 25/18* (2023.01)
G11C 5/02 (2006.01) *G11C 16/04* (2006.01)
G11C 7/16 (2006.01) *H01L 23/00* (2006.01)

(21) International Application Number:
PCT/CN2025/088886

(22) International Filing Date:
14 April 2025 (14.04.2025)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
202411412243.6 10 October 2024 (10.10.2024) CN

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(54) Title: SEMICONDUCTOR STRUCTURES, SEMICONDUCTOR DEVICES, COMPUTING-IN-MEMORY DEVICES, ELECTRONIC APPARATUS, AND OPERATION METHODS THEREOF

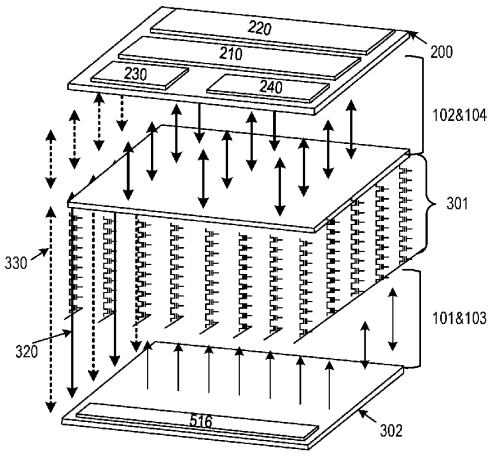

FIG. 10

(57) Abstract: A disclosed semiconductor device comprises a first semiconductor structure comprising an analog-to-digital converter circuit and a data processing circuit; and a second semiconductor structure comprising a memory array and a peripheral circuit coupled to the memory array; wherein the analog-to-digital converter circuit is coupled with the memory array and configured to convert analog computation information based on a first operation performed by the memory array into digital information, and the data processing circuit is coupled with the analog-to-digital converter circuit and configured to perform a second operation based on the digital information.

[Continued on next page]

WO 2026/076911 A1

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(81) Designated States *(unless otherwise indicated, for every kind of national protection available)*: AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BN, BR, BW, BY, BZ, CA, CH, CL, CN, CO, CR, CU, CV, CZ, DE, DJ, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IQ, IR, IS, IT, JM, JO, JP, KE, KG, KH, KN, KP, KR, KW, KZ, LA, LC, LK, LR, LS, LU, LY, MA, MD, MG, MK, MN, MU, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PA, PE, PG, PH, PL, PT, QA, RO, RS, RU, RW, SA, SC, SD, SE, SG, SK, SL, ST, SV, SY, TH, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UY, UZ, VC, VN, WS, ZA, ZM, ZW.

(84) Designated States *(unless otherwise indicated, for every kind of regional protection available)*: ARIPO (BW, CV, GH, GM, KE, LR, LS, MW, MZ, NA, RW, SC, SD, SL, ST, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, RU, TJ, TM), European (AL, AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, ME, MK, MT, NL, NO, PL, PT, RO, RS, SE, SI, SK, SM, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, KM, ML, MR, NE, SN, TD, TG).

Published:

— *with international search report (Art. 21(3))*